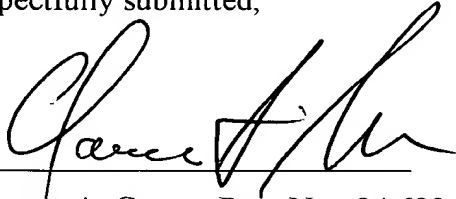


## REMARKS

In accordance with 37 C.F.R. §1.121 (as amended on 11/7/2000) the rewritten claim(s) above are shown on separate page(s) marked up to show all the changes relative to the previous version of that section.

Respectfully submitted,



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8 March 01

Date

Application entitled: QUANTUM WELL INTERMIXING

## MARKED UP CLAIM(S)

### CLAIMS

5. A method according to ~~any preceding claim~~claim 1, including the step of masking a portion of the structure to control the degree of radiation damage.
8. A method according to ~~any of claims 5 to 7~~claim 5, in which the mask is selected from a group consisting of binary masks, phase masks, gray masks, dielectric or metal masks, and photoresist masks.
9. A method according to ~~any preceding claim~~claim 1, in which spatial control of intermixing is controlled using a variable profile mask pattern.
10. A method according to ~~any preceding claim~~claim 1 further comprising the steps of forming a photoresist on the structure and differentially exposing regions of the photoresist in a spatially selective manner in dependence on the degree of quantum well intermixing required, and subsequently developing the photoresist.
13. A method according to ~~any of claims 10 to 12~~claim 10, in which the photoresist is applied to a masking layer.
15. A method according to ~~claims 13 or 14~~, further comprising the step of etching the structure with the developed photoresist in situ to provide a differentially etched masking layer.
16. A method according to ~~any preceding claim~~claim 1, in which an electron cyclotron resonance system is used to generate a plasma, wherein the microwave power of the ECR system is between 300 and 3000 W, more preferably between 1000 and 2000 W, the process temperature is between 25 and 500°C, more preferably between 25 and 200°C, the process pressure is between 0.1 and 100 mTorr, more

preferably between 20 and 50 mTorr, and the exposure time is between 30 seconds and 1 hour, more preferably between 4 and 14 minutes.